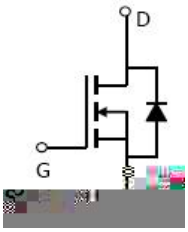
A	2019-4-18	ALL	AO3400		
B	2020-5-28	1			

Rev.A Apr.-2019

SOT-23 N MOS - CHANNEL MOSFET in a SOT-23 Plastic Package.

V_{DS} (V) = 30V
I_D = 5.8 A (V_{GS} = 10V)
$R_{DS(ON)}$ < 28mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 33mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 52mΩ (V_{GS} = 2.5V)
无卤产品。HF Product.

This device is suitable for use as a load switch or in PWM applications.

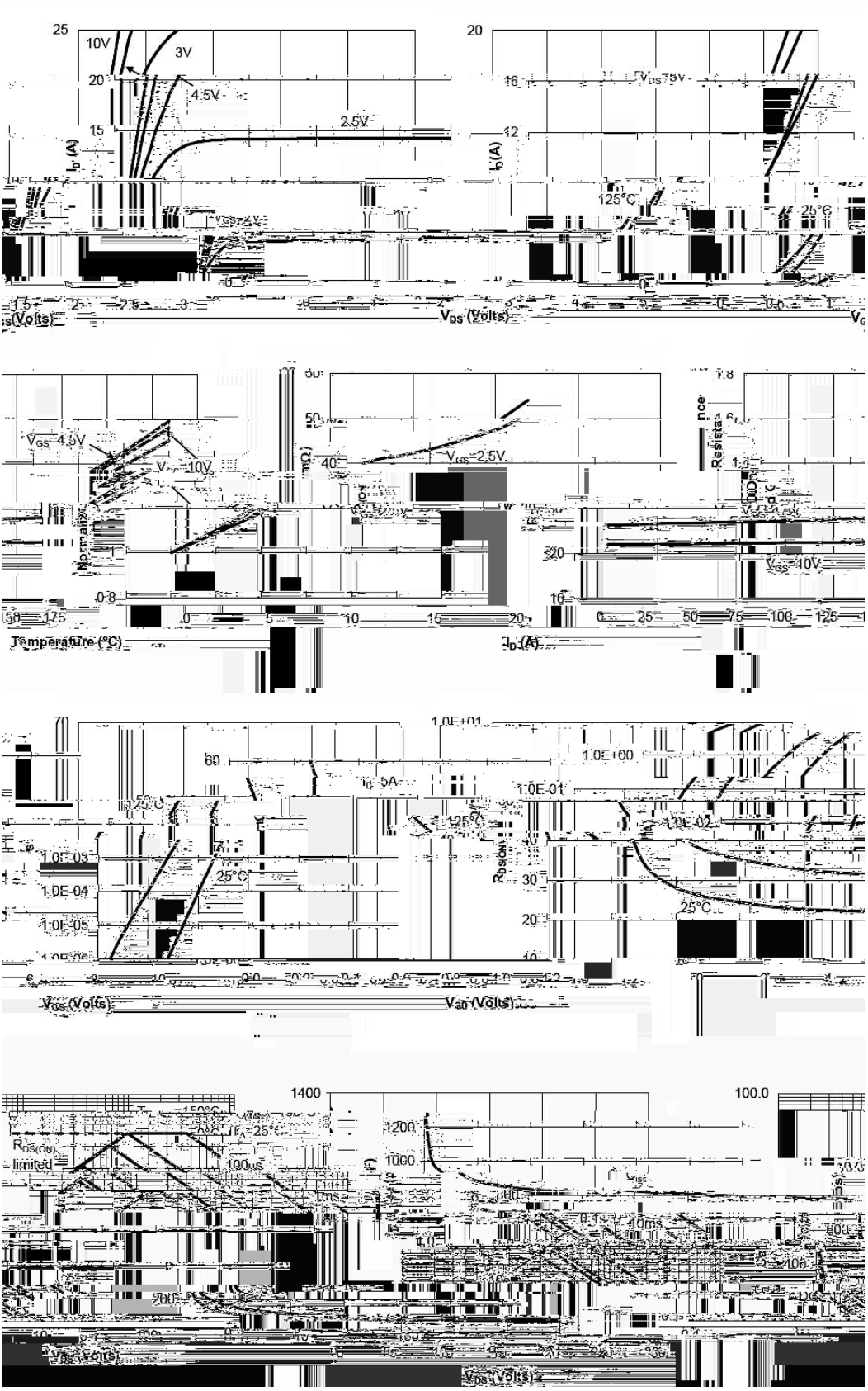


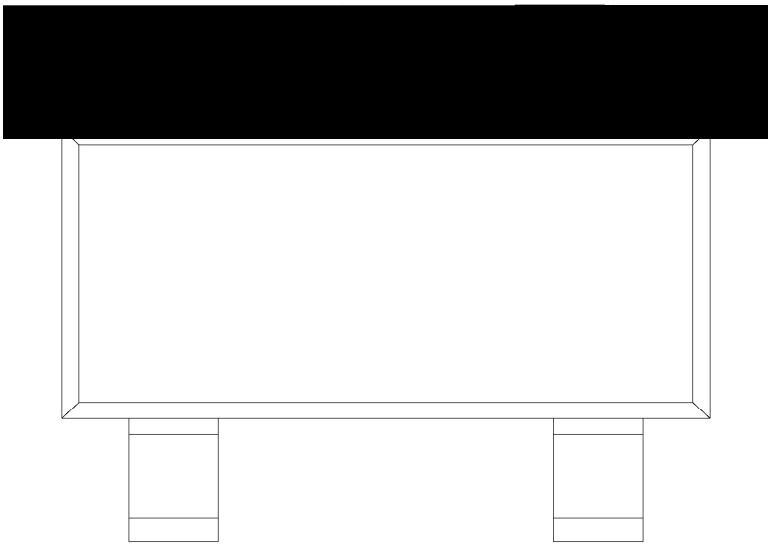


PIN1 G PIN 2 S PIN 3 D

Marking	A0H

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	V_{DS}=15V V_{GS}=0V f=1MHz		823	1030	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V, f=1MHz		1.2	3.6	Ω
Total Gate Charge	Q_g	V_{GS}=4.5V, V_{DS}=15V, I_D=5.8A		9.7	12	nC
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3.1		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=10V R_L=2.7Ω V_{DS}=15V R_{GEN}=3Ω		3.3	5	ns
Turn–On Rise Time	t_r			4.8	7	
Turn–Off Delay Time	$t_{d(off)}$			26.3	40	
Turn–Off Fall Time	t_f			4.1	6	
Body Diode Reverse Recovery Time	t_{rr}	I_F=5A dI/dt=100A/μs		16	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=5A dI/dt=100A/μs		8.9	12	nC

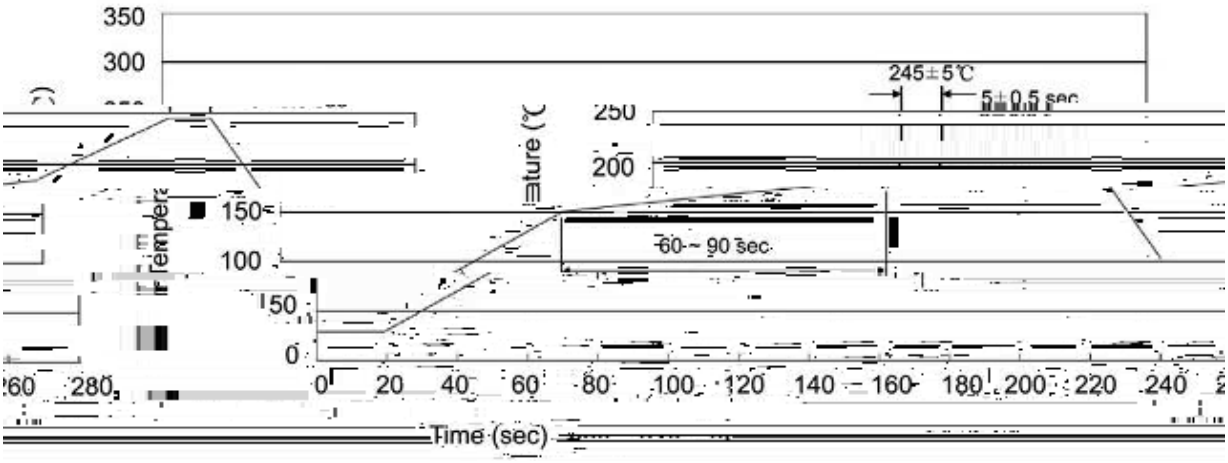

10V
3V
4.5V
2.5V
I_D (A)
V_{DS} (Volts)
V_{GS}=5V
125°C
25°C
V_{GS}=4.5V
V_{GS}=2.5V
V_{GS}=10V
Normalized
Temperature (°C)
I_D (A)
Resistance
I_S=5A
125°C
25°C
V_{GS} (Volts)
V_{SD} (Volts)
$R_{DS(ON)}$ limited
100µs
1ms
10ms
100ms
1s
10s
DC
V_{DS} (Volts)



A0

H

Note:



		Note:	
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.	
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type
封